Notice of Allowability	Application No.	Applicant(s)
	10/779,790	TADA ET AL.
	Examiner	Art Unit
	Thinh T Nguyen	2818
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap) or other appropriate communicatio (IGHTS. This application is subject)	oplication. If not included n will be mailed in due course. THIS
1. This communication is responsive to 8/12/2004.		
2. ⊠ The allowed claim(s) is/are <u>17-26</u> .		
3. $igotimes$ The drawings filed on <u>18 February 2004</u> are accepted by t	the Examiner.	
 4. Acknowledgment is made of a claim for foreign priority u a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" 	e been received. e been received in Application No. <u>1</u> comments have been received in this	national stage application from the
noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be subm		R'S AMENDMENT or NOTICE OF
INFORMAL PATENT APPLICATION (PTO-152) which give	res reason(s) why the oath or declar	ation is deficient.
 CORRECTED DRAWINGS (as "replacement sheets") mu (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1) each sheet. Replacement sheet(s) should be labeled as such in the sheet of the s	son's Patent Drawing Review(PTC - 's Amendment / Comment or in the 1.84(c)) should be written on the draw the header according to 37 CFR 1.121	Office action of ings in the front (not the back) of (d).
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT 	osit of BIOLOGICAL MATERIAL FOR THE DEPOSIT OF BIOLOGIC	must be submitted. Note the CAL MATERIAL.
Attachment(s)	E Nation of Information	Potent Application (PTO 152)
 Notice of References Cited (PTO-892) D Notice of Draftperson's Patent Drawing Review (PTO-948) 		Patent Application (PTO-152) v (PTO-413)
	Paper No./Mail Da	ate
 Information Disclosure Statements (PTO-1449 or PTO/SB/ Paper No./Mail Date 	08), 7. ⊠ Examiner's Amend	iment/Comment
4. Examiner's Comment Regarding Requirement for Deposit	_ =	ent of Reasons for Allowance
of Biological Material	9.	
Bavid Nelms		
Supervisory, Patent Examiner		
Technology:Center 2800		

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DETAILED ACTION

1. Applicant election of claims 17-26 without traverse for prosecution in the communication

with the Office on 8/12/2004 is acknowledged.

Examiner's Amendment.

2. An examiner's amendment to the record appears below. Should the changes and/or

additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR

1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the

payment of the issue fee.

--Since Applicant elected claims 17-26 for prosecution without traverse, non-elected

claims 1-16 are cancelled --.

Specification

3. The specification has been checked to the extent necessary to determine the presence

of all possible minor errors. However, the applicant cooperation is requested in correcting any

errors of which the applicant may become aware in the specification.

Reason for allowance

4. Claims 17-26 are allowed. The following is an examiner's statement of reason for allowance:

None of the references of record teaches or suggests the claimed LATERAL HIGH

BREAKDOWN VOLTAGE MOSFET AND DEVICE PROVIDED THEREWITH having the limitations:

- -- " comprising a buried layer formed in a region of a semiconductor substrate "--
- --" the gate oxide film comprises a thickness in which an electric field value of an absolute maximum rated voltage between a source and a drain is equal to or less than 4 MV/cm, and a total amount of impurities in the drain diffused layer is equal to or more than 2.times.10.sup.12/cm.sup.2; and a lateral low breakdown voltage MOSFET "-- and all other limitations as recited in claim 17.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

5. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d) in parent Application 10/308,200 which papers have been placed of record in the file.

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Conclusion

6. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Zambrano (US patent 5,300,451) disclosed a process for forming a buried drain or

collector region in monolithic semiconductor devices

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thinh T Nguyen whose telephone number is 571-272-1790.

The examiner can normally be reached on Monday-Friday 9:00am-6:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached at 571-272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Thinh T Nguyen

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David Nelms Supervisory Patent Examiner

Technology Center 2800

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